

IN THE CLAIMS:

Please cancel claims 2 and 4 without prejudice. Kindly amend claims 1 and 3 as follows.

1. (Currently amended) A method for inspecting wire breaking of a semiconductor integrated circuit in a non-contact manner, comprising the steps of:

maintaining a semiconductor integrated circuit-~~(1)~~ in a state where a predetermined voltage is being applied thereto;

two-dimensionally scanning and irradiating a two-dimensional circuit of the semiconductor integrated circuit by using an ultrashort light pulse-~~(2)~~, wherein the ultrashort light pulse has a wavelength equal to or larger than 300 nanometers and equal to or smaller than 2 microns, time average energy equal to or larger than 0.1 mW and equal to or smaller than 10 W, and a pulse width equal to or larger than 1 femtosecond and equal to or smaller than 10 picoseconds;

detecting an electromagnetic wave-~~(3)~~ radiated from a position irradiated with the ultrashort light pulse on the semiconductor integrated circuit; and

detecting wire breaking of the irradiated position based on presence and absence or intensity of the electromagnetic wave.

2. (Canceled)

3. (Currently amended) An apparatus that inspects wire breaking of a semiconductor integrated circuit, comprising:

a voltage applying device-~~(12)~~ that maintains a semiconductor integrated circuit in a state where a predetermined voltage is being applied thereto;

a light pulse source-(14) that generates an ultrashort light pulse-(2), wherein the light pulse source is a mode lock Ti-sapphire laser or femto-second fiber laser capable of generating the ultrashort light pulse that has a wavelength equal to or larger than 300 nanometers and equal to or smaller than 2 microns, time average energy equal to or larger than 0.1 mW and equal to or smaller than 10 W, and a pulse width equal to or larger than 1 femtosecond and equal to or smaller than 10 picoseconds;

a scanning device-(16) that two-dimensionally scans and irradiates a two-dimensional circuit of the semiconductor integrated circuit by using the ultrashort light pulse (2);

an electromagnetic wave detection device-(18) that detects an electromagnetic wave (3)-radiated from a position irradiated with the ultrashort light pulse on the semiconductor integrated circuit; and

a wire breaking detection device-(20) that detects wire breaking of the irradiated position based on presence and absence or intensity of the electromagnetic wave.

4. (Canceled)